



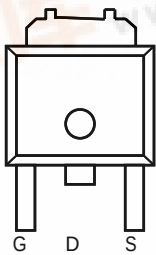
ALPHA & OMEGA
SEMICONDUCTOR, LTD.

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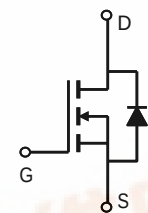
AOD442, AOD442L (Green Product)
N-Channel Enhancement Mode Field Effect Transistor

General Description The AOD442 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications. AOD442L (Green Product) is offered in a lead-free package.	Features $V_{DS} (V) = 60V$ $I_D = 38A$ $R_{DS(ON)} < 20m\Omega (V_{GS} = 10V)$ $R_{DS(ON)} < 25m\Omega (V_{GS} = 4.5V)$
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TO-252
D-PAK



Top View
Drain Connected to
Tab



Absolute Maximum Ratings T _A =25°C unless otherwise noted					
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current ^{B,G}	T _C =25°C ^G	I _D	38	A	
	T _C =100°C ^B		27		
Pulsed Drain Current		I _{DM}	60		
Avalanche Current ^C		I _{AR}	30		A
Repetitive avalanche energy L=0.1mH ^C		E _{AR}	140		mJ
Power Dissipation ^B	T _C =25°C	P _D	60	W	
	T _C =100°C		30		
Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 175	°C	

Thermal Characteristics					
Parameter	Symbol	Typ	Max	Units	
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	$t \leq 10s$	17.4	25	$^{\circ}C/W$
Maximum Junction-to-Ambient ^A		Steady-State	51	60	$^{\circ}C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	Steady-State	1.8	2.5	$^{\circ}C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	1	2.1	3	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	60			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		16 31	20	mΩ
		V _{GS} =4.5V, I _D =20A		20	25	
						mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A	4.5	5.6		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.74	1	V
I _S	Maximum Body-Diode Continuous Current				4	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, f=1MHz		1920	2300	pF
C _{oss}	Output Capacitance			155		pF
C _{rss}	Reverse Transfer Capacitance			116		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		0.65	0.8	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =30V, I _D =20A		47.6	68	nC
Q _g (4.5V)	Total Gate Charge			24.2	30	nC
Q _{gs}	Gate Source Charge			6		nC
Q _{gd}	Gate Drain Charge			14.4		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =30V, R _L =1.5Ω, R _{GEN} =3Ω		7.4		ns
t _r	Turn-On Rise Time			5.1		ns
t _{D(off)}	Turn-Off DelayTime			28.2		ns
t _f	Turn-Off Fall Time			5.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=100A/μs		34	41	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, dI/dt=100A/μs		46		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any a given application depends on the user's specific board design, and the maximum temperature fo 175°C may be used if the PCB allows it.

B: The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=175°C.

D: The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

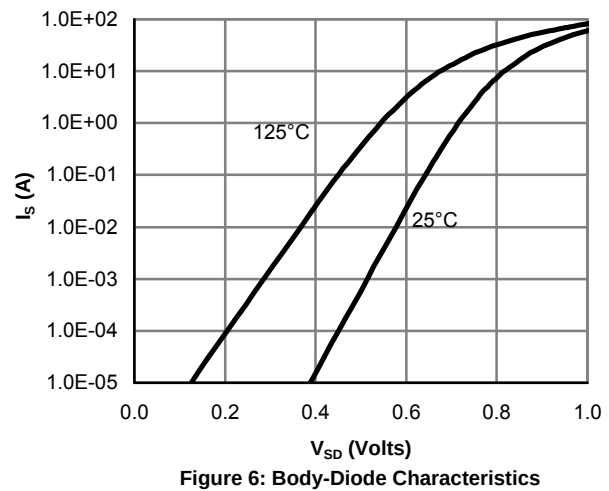
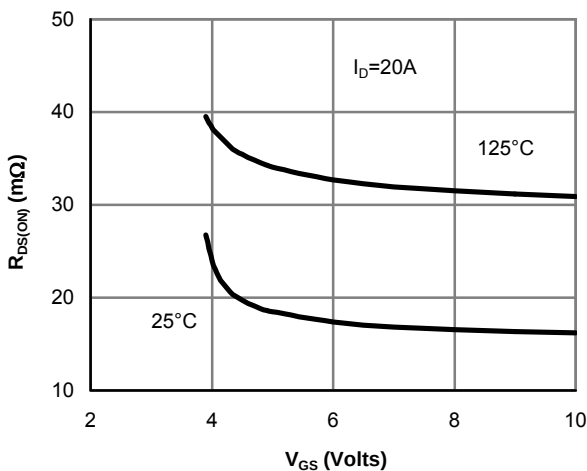
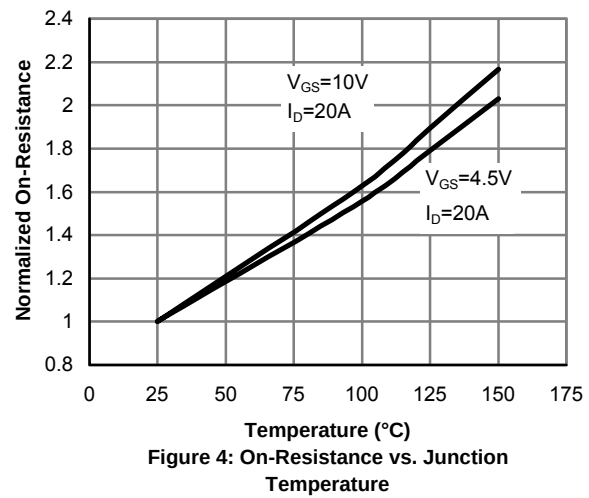
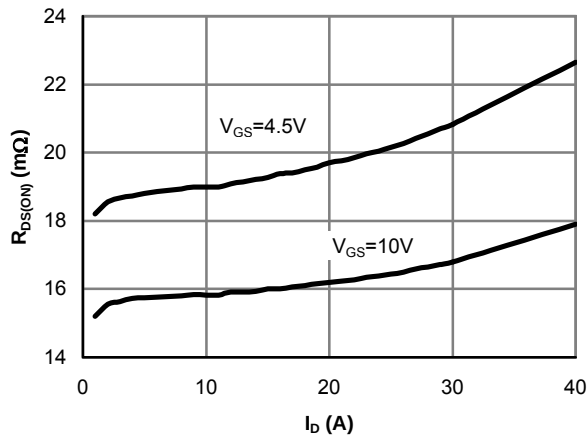
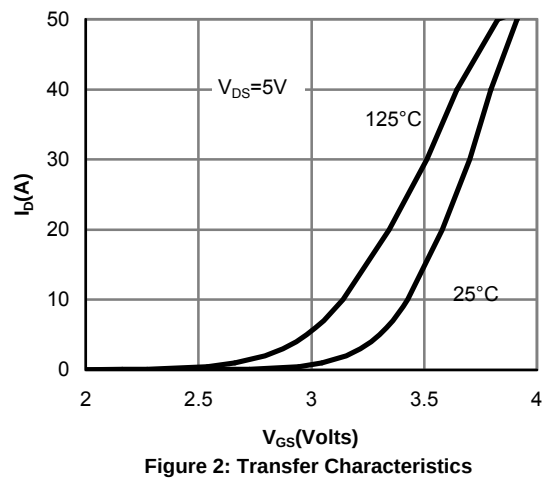
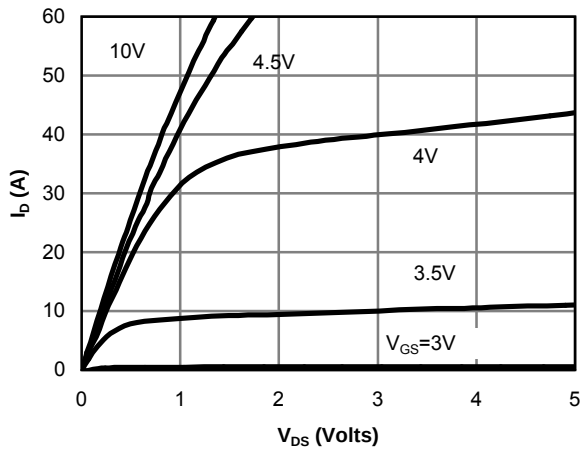
F: These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C.

G: The maximum current rating is limited by bond-wires.

H: These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



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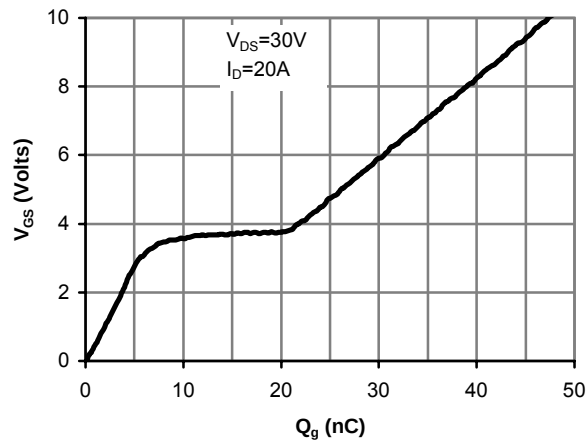


Figure 7: Gate-Charge Characteristics

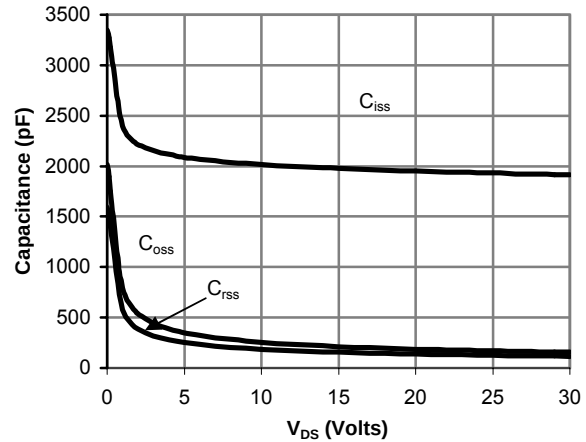


Figure 8: Capacitance Characteristics

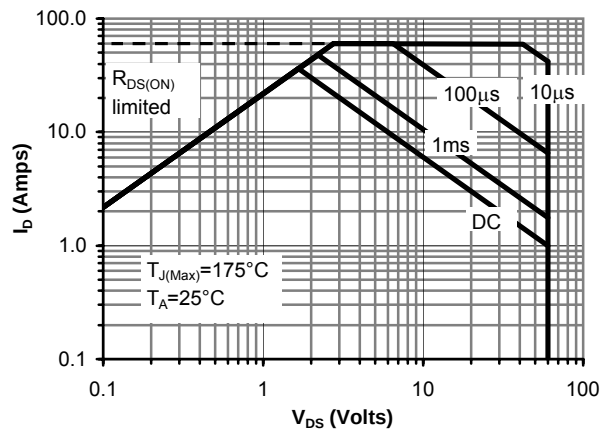


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

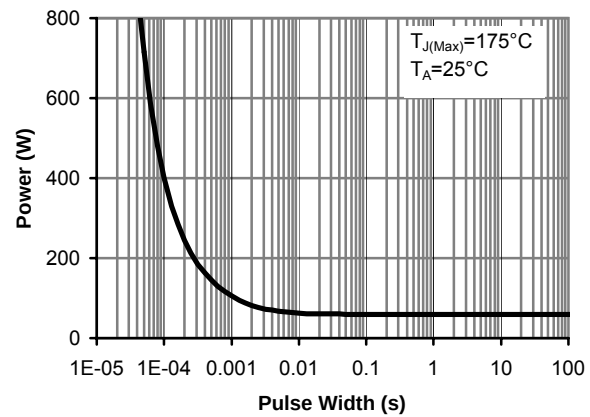


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

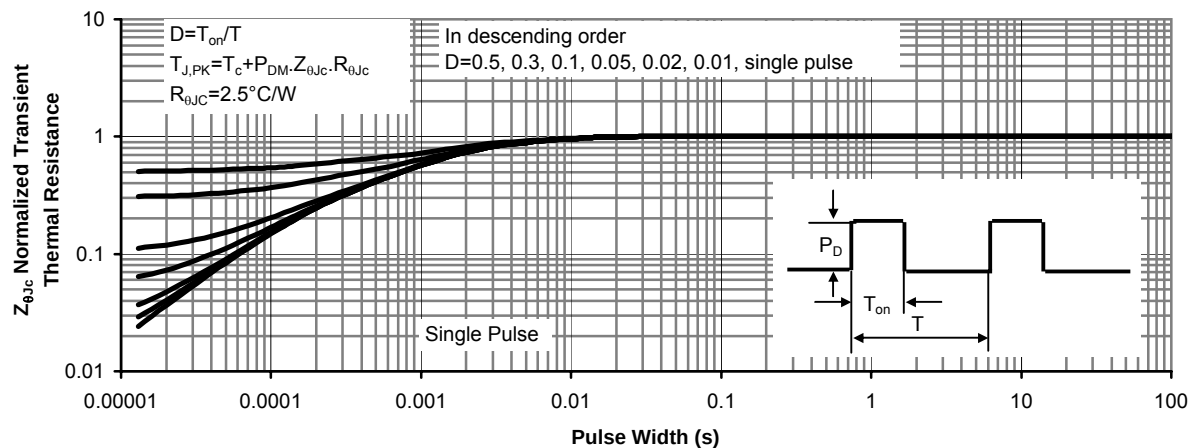


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

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